



FDMS003N08C

N-Channel Shielded Gate PowerTrench® MOSFET 80 V, 147 A, 3.1 mΩ

Features

- Shielded Gate MOSFET Technology
- Max $r_{DS(on)}$ = 3.1 mΩ at $V_{GS} = 10$ V, $I_D = 56$ A
- Max $r_{DS(on)}$ = 8.1 mΩ at $V_{GS} = 6$ V, $I_D = 28$ A
- 50% lower Q_{rr} than other MOSFET suppliers
- Lowers switching noise/EMI
- MSL1 robust package design
- 100% UIL tested
- RoHS Compliant

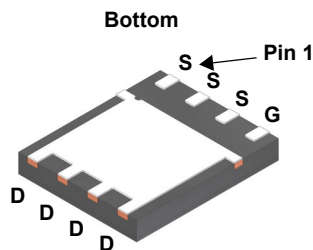
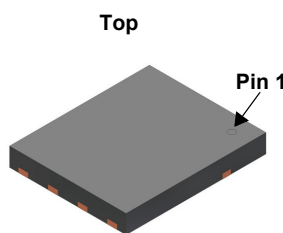


General Description

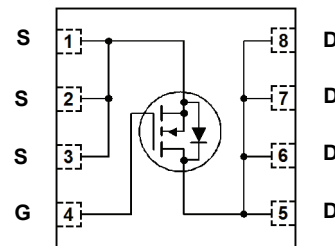
This N-Channel MV MOSFET is produced using ON Semiconductor's advanced PowerTrench® process that incorporates Shielded Gate technology. This process has been optimized to minimise on-state resistance and yet maintain superior switching performance with best in class soft body diode.

Applications

- Primary DC-DC MOSFET
- Synchronous Rectifier in DC-DC and AC-DC
- Motor Drive
- Solar



Power 56



MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rated	Units
V_{DS}	Drain to Source Voltage	80	V
V_{GS}	Gate to Source Voltage	± 20	V
I_D	Drain Current -Continuous	$T_C = 25^\circ\text{C}$ (Note 5)	147
	-Continuous	$T_C = 100^\circ\text{C}$ (Note 5)	92
	-Continuous	$T_A = 25^\circ\text{C}$ (Note 1a)	22
	-Pulsed	(Note 4)	658
E_{AS}	Single Pulse Avalanche Energy	(Note 3)	486
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	125
	Power Dissipation	$T_A = 25^\circ\text{C}$ (Note 1a)	2.7
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	1	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	45	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS003N08C	FDMS003N08C	Power 56	13"	12 mm	3000 units

Electrical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}$, $V_{GS} = 0\text{ V}$	80			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^\circ\text{C}$		60		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 64\text{ V}$, $V_{GS} = 0\text{ V}$			1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{ V}$, $V_{DS} = 0\text{ V}$			100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 310\text{ }\mu\text{A}$	2.0	2.9	4.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 310\text{ }\mu\text{A}$, referenced to $25\text{ }^\circ\text{C}$		-8.2		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}$, $I_D = 56\text{ A}$		2.6	3.1	m Ω
		$V_{GS} = 6\text{ V}$, $I_D = 28\text{ A}$		3.8	8.1	
		$V_{GS} = 10\text{ V}$, $I_D = 56\text{ A}$, $T_J = 125\text{ }^\circ\text{C}$		4.3	5.2	
g_{FS}	Forward Transconductance	$V_{DS} = 5\text{ V}$, $I_D = 56\text{ A}$		123		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 40\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$		3820	5350	pF
C_{oss}	Output Capacitance			1335	1870	pF
C_{rss}	Reverse Transfer Capacitance			44	80	pF
R_g	Gate Resistance		0.1	0.6	1.3	Ω

Switching Characteristics

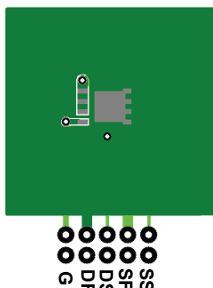
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 40\text{ V}$, $I_D = 56\text{ A}$, $V_{GS} = 10\text{ V}$, $R_{GEN} = 6\text{ }\Omega$		20	36	ns
t_r	Rise Time			8	16	ns
$t_{d(off)}$	Turn-Off Delay Time			40	64	ns
t_f	Fall Time			12	23	ns
Q_g	Total Gate Charge	$V_{GS} = 0\text{ V to }10\text{ V}$	$V_{DD} = 40\text{ V}$, $I_D = 56\text{ A}$	52	73	nC
Q_g	Total Gate Charge	$V_{GS} = 0\text{ V to }6\text{ V}$		33	46	nC
Q_{gs}	Gate to Source Charge			17		nC
Q_{gd}	Gate to Drain "Miller" Charge			10		nC
Q_{oss}	Output Charge	$V_{DD} = 40\text{ V}$, $V_{GS} = 0\text{ V}$		77		nC
Q_{sync}	Total Gate Charge Sync	$V_{DS} = 0\text{ V}$, $I_D = 56\text{ A}$		44		nC

Drain-Source Diode Characteristics

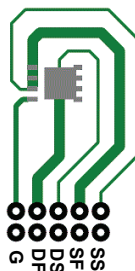
V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}$, $I_S = 2.2\text{ A}$ (Note 2)		0.7	1.2	V
		$V_{GS} = 0\text{ V}$, $I_S = 56\text{ A}$ (Note 2)		0.8	1.3	
t_{rr}	Reverse Recovery Time	$I_F = 28\text{ A}$, $di/dt = 300\text{ A}/\mu\text{s}$		28	45	ns
Q_{rr}	Reverse Recovery Charge			53	84	nC
t_{rr}	Reverse Recovery Time	$I_F = 28\text{ A}$, $di/dt = 1000\text{ A}/\mu\text{s}$		23	36	ns
Q_{rr}	Reverse Recovery Charge			121	194	nC

Notes:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a $1.5 \times 1.5\text{ in.}$ board of FR-4 material. $R_{\theta CA}$ is determined by the user's board design.



a. $45\text{ }^\circ\text{C/W}$ when mounted on a 1 in^2 pad of 2 oz copper.



b. $115\text{ }^\circ\text{C/W}$ when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < $300\text{ }\mu\text{s}$, Duty cycle < 2.0%.

3. E_{AS} of 486 mJ is based on starting $T_J = 25\text{ }^\circ\text{C}$; N-ch: $L = 3\text{ mH}$, $I_{AS} = 18\text{ A}$, $V_{DD} = 80\text{ V}$, $V_{GS} = 10\text{ V}$. 100% test at $L = 0.1\text{ mH}$, $I_{AS} = 57\text{ A}$.

4. Pulsed I_D please refer to Fig 11 SOA graph for more details.

5. Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted.

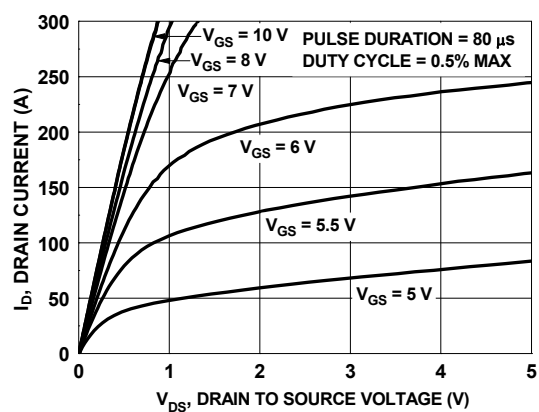


Figure 1. On Region Characteristics

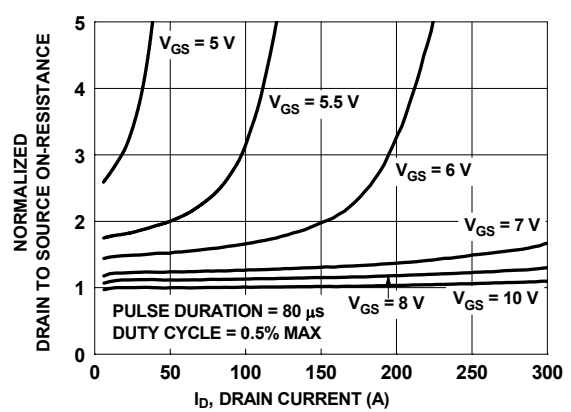


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

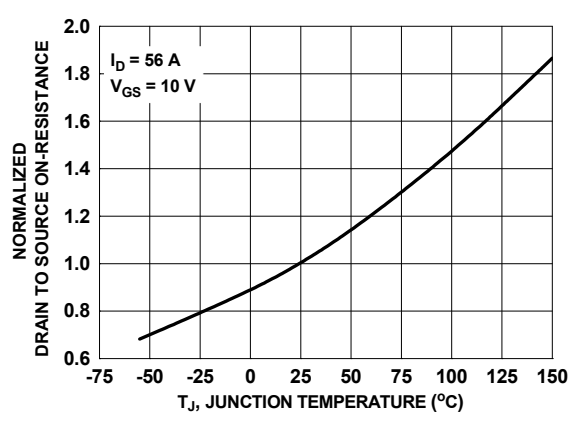


Figure 3. Normalized On Resistance vs. Junction Temperature

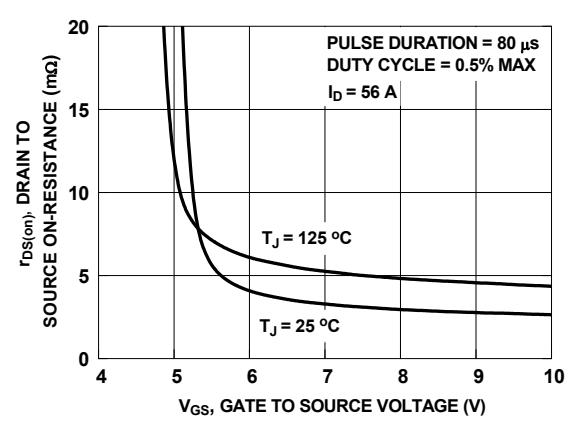


Figure 4. On-Resistance vs. Gate to Source Voltage

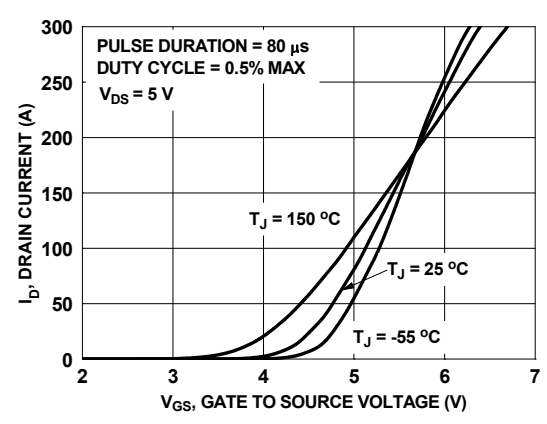


Figure 5. Transfer Characteristics

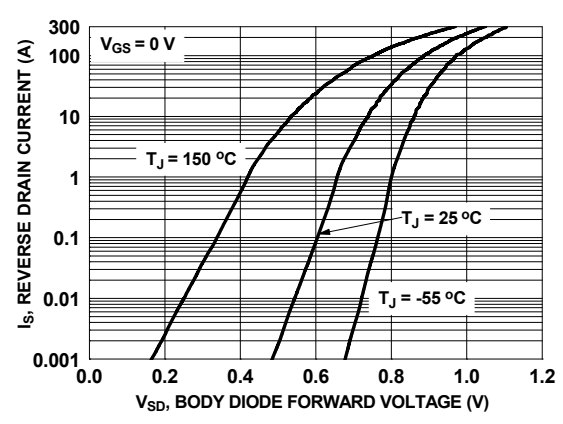


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted.

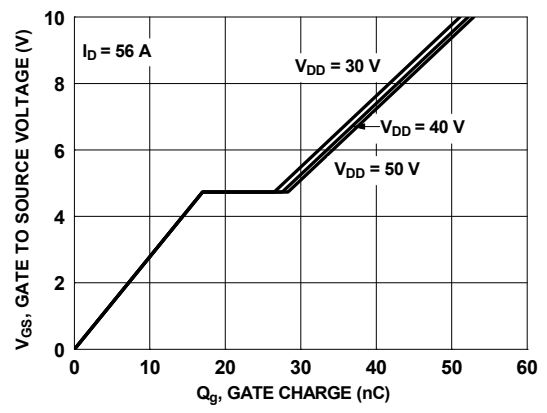


Figure 7. Gate Charge Characteristics

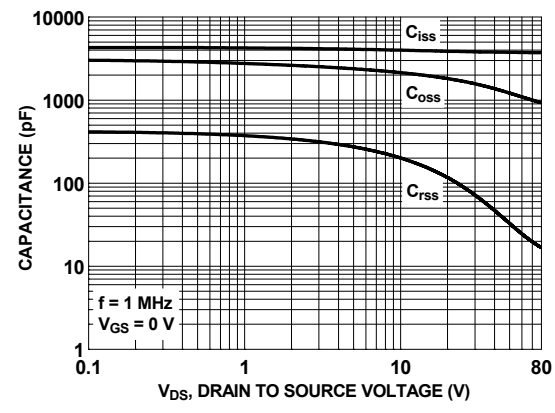


Figure 8. Capacitance vs. Drain to Source Voltage

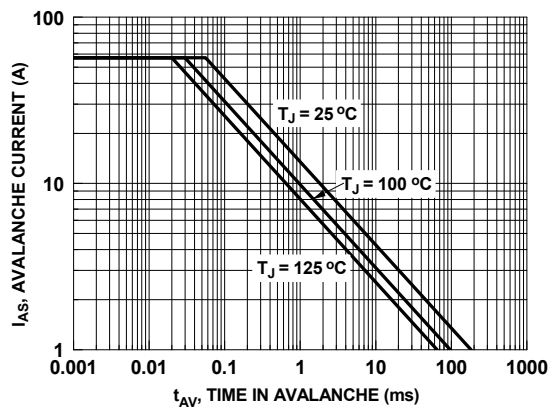


Figure 9. Unclamped Inductive Switching Capability

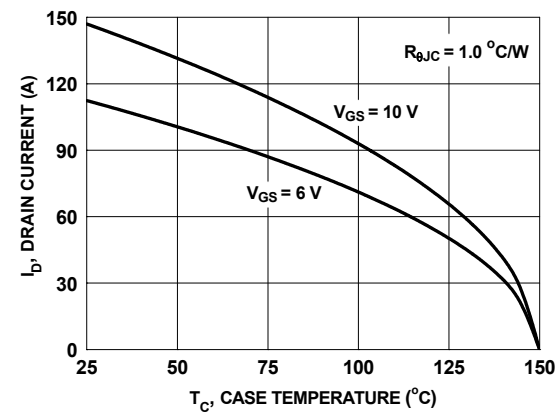


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

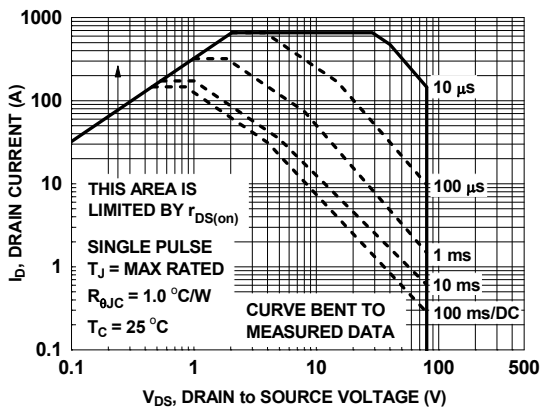


Figure 11. Forward Bias Safe Operating Area

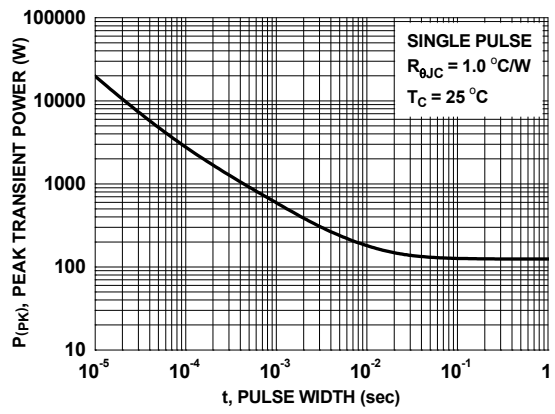


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted.

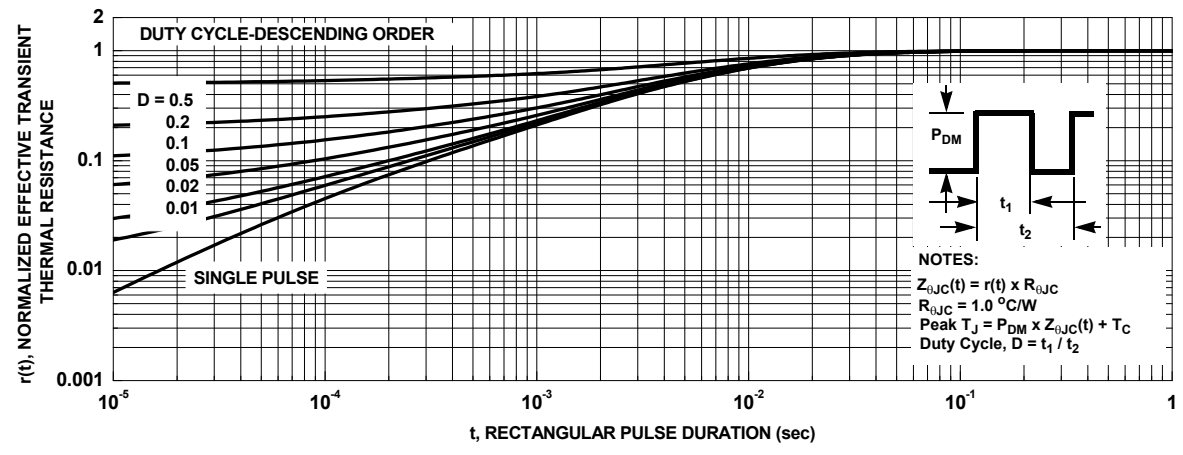
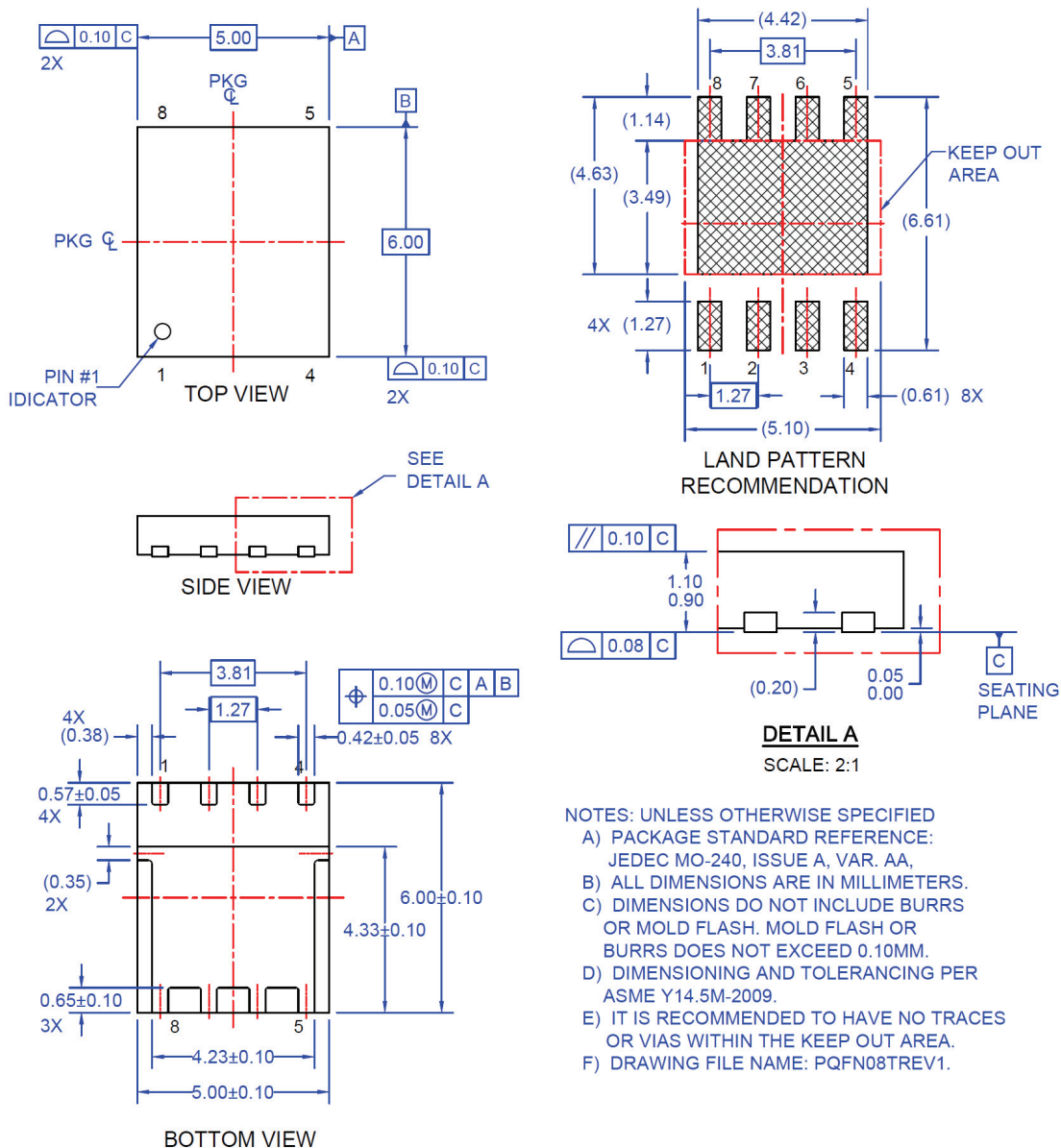


Figure 13. Junction-to-Case Transient Thermal Response Curve

Dimensional Outline and Pad Layout



- NOTES: UNLESS OTHERWISE SPECIFIED
- PACKAGE STANDARD REFERENCE: JEDEC MO-240, ISSUE A, VAR. AA,
 - ALL DIMENSIONS ARE IN MILLIMETERS.
 - DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
 - DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
 - IT IS RECOMMENDED TO HAVE NO TRACES OR VIAS WITHIN THE KEEP OUT AREA.
 - DRAWING FILE NAME: PQFN08TREV1.

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